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15EE34

Third Semester B.E. Degree Examination, Feb./Mar. 2022
Analog Electronic Circuits

Time: 3 hrs.

Max. Marks: 80

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- 1 a. Draw and explain series negative clipper with the help of output waveform and transfer characteristics. (04 Marks)
- b. Derive an expression for $S(iC_O)$ and $S(V_{BE})$ for fixed bias. (06 Marks)
- c. Determine the following for the fixed-bias configuration of Fig.Q1(c).
(i) I_{BQ} and I_{CQ} (ii) V_{CEQ} (iii) V_B and V_C

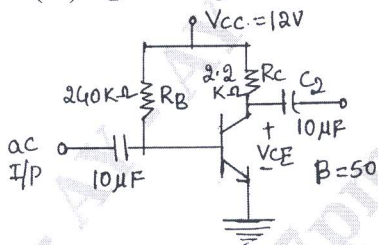


Fig.Q1(c)

(06 Marks)

OR

- 2 a. Explain Emitter bias circuit, with the help of BE loop and CE loop. Write necessary equation. (08 Marks)
- b. Design a suitable circuit represented by the box shown in Fig.Q2(b), which had input and output waveforms as indicated.

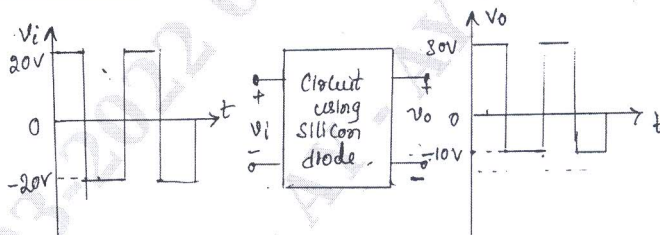
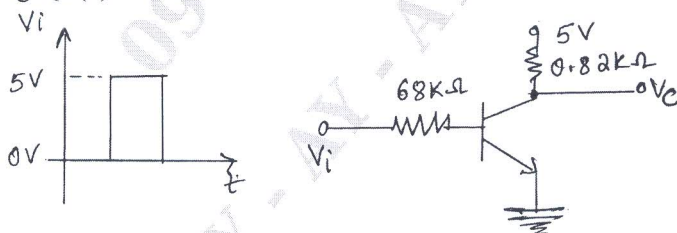


Fig.Q2(b)

(04 Marks)

- c. Fig.Q2(c) shows the transistor switch check whether the circuit works properly.



$V_{CE} = 0.7V$
 $V_{CE(SAT)} = 0.15V$
 $I_{CEO} = 10 \mu A$
 $\beta_{dc} = h_{FE} = 125$

Fig.Q2(c)

(04 Marks)

Module-2

- 3 a. Define h-parameters. Hence derive h-parameter model of a CE – BJT. (06 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

- b. For the common base configuration of Fig.Q3(b). $I_E = 4 \text{ mA}$, $\alpha = 0.991$. An ac signal of 3 mV is applied between the base and emitter terminals. If $R_L = 610 \Omega$. Calculate
 (i) r_v and z_i (ii) A_v and A_i

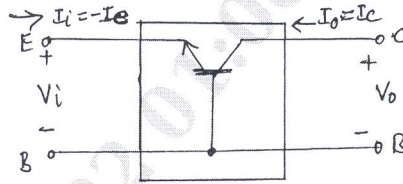


Fig.Q3(b)

(04 Marks)

- c. For the circuit shown in Fig.Q3(c),
 (i) Determine r_c (ii) Find z_i , z_o , A_v and A_i (with $r_o = \infty \Omega$)

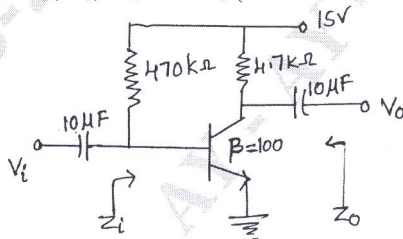


Fig.Q3(c)

(06 Marks)

OR

- 4 a. Draw the emitter follower circuit. Derive expression for (i) z_i (ii) z_o (iii) A_v using re model. (08 Marks)
 b. Derive the expressions for Miller's effect capacitance. (08 Marks)

Module-3

- 5 a. Explain the need of cascading amplifier? Draw and explain the block diagram of two stage cascade amplifier. (06 Marks)
 b. For the amplifier circuit shown in Fig.Q5(b), calculate z_i , z_o , A_i and A_v .

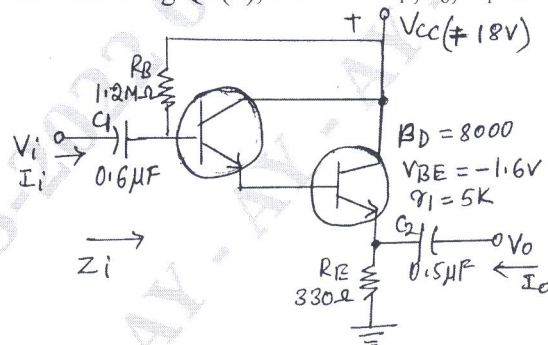


Fig.Q5(b)

(04 Marks)

- c. Derive the expression for input resistance (R_{if}) for a current series feedback. (06 Marks)

OR

- 6 a. With necessary equivalent diagram, obtain the expression for z_{in} , A_v , z_o for a Darlington Emitter follower. (10 Marks)
 b. An amplifier with open loop voltage gain of 1000 deliver 10W of power output at 10% second harmonic distortion when i/p is 10 mV. If 40 dB negative feedback is applied and output power is to remain at 10W, determine required input signal V_s and second harmonic distortion with feedback. (06 Marks)

Module-4

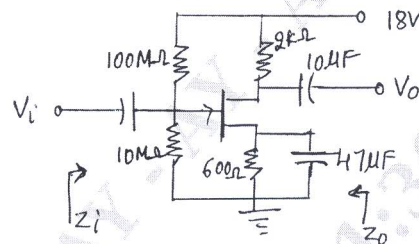
- 7 a. Show that series fed directly coupled class A power amplifiers has a maximum power efficiency of 25%. (10 Marks)
 b. With a neat diagram, Explain the working of R-C phase shift oscillator. (06 Marks)

OR

- 8 a. Compare RC phase shift oscillator with wein bridge oscillator. (04 Marks)
 b. The following data are available for the Colpitts oscillator.
 $C_1 = 1 \text{ nF}$, $C_2 = 99 \text{ nF}$, $L = 1.5 \text{ mH}$
 $L_{RFC} = 0.5 \text{ mH}$ $C_c = 10 \text{ }\mu\text{F}$, $h_{fc} = 110$
 (i) Calculate the frequency of oscillation
 (ii) Check to make sure that the condition for oscillation is satisfied. (06 Marks)
 c. Calculate the peak power dissipated in each transistor of a class B, push pull power amplifier if $V_{CC} = 15\text{V}$ and $R'_L = 5\Omega$. (06 Marks)

Module-5

- 9 a. Draw JFET amplifier using fixed bias configuration. Derive z_i , z_o , A_v for small signal model. (10 Marks)
 b. For the JFET amplifier shown in Fig.Q9(b).
 (i) Calculate z_i and z_o (ii) Calculate A_v (iii) Find V_o if $V_i = 25\text{mV(rms)}$



$I_{DSS} = 12 \text{ mA}$
 $V_p = -3\text{V}$
 $V_{os} = 10 \text{ }\mu\text{s}$
 $V_{GSQ} = -1\text{V}$

Fig.Q9(b)

(06 Marks)

OR

- 10 a. Explain the structure of the Depletion mode MOSFET. (08 Marks)
 b. Define Transconductance g_m . Derive an expression for g_m . (04 Marks)
 c. List the difference between FET and BJT. (04 Marks)
